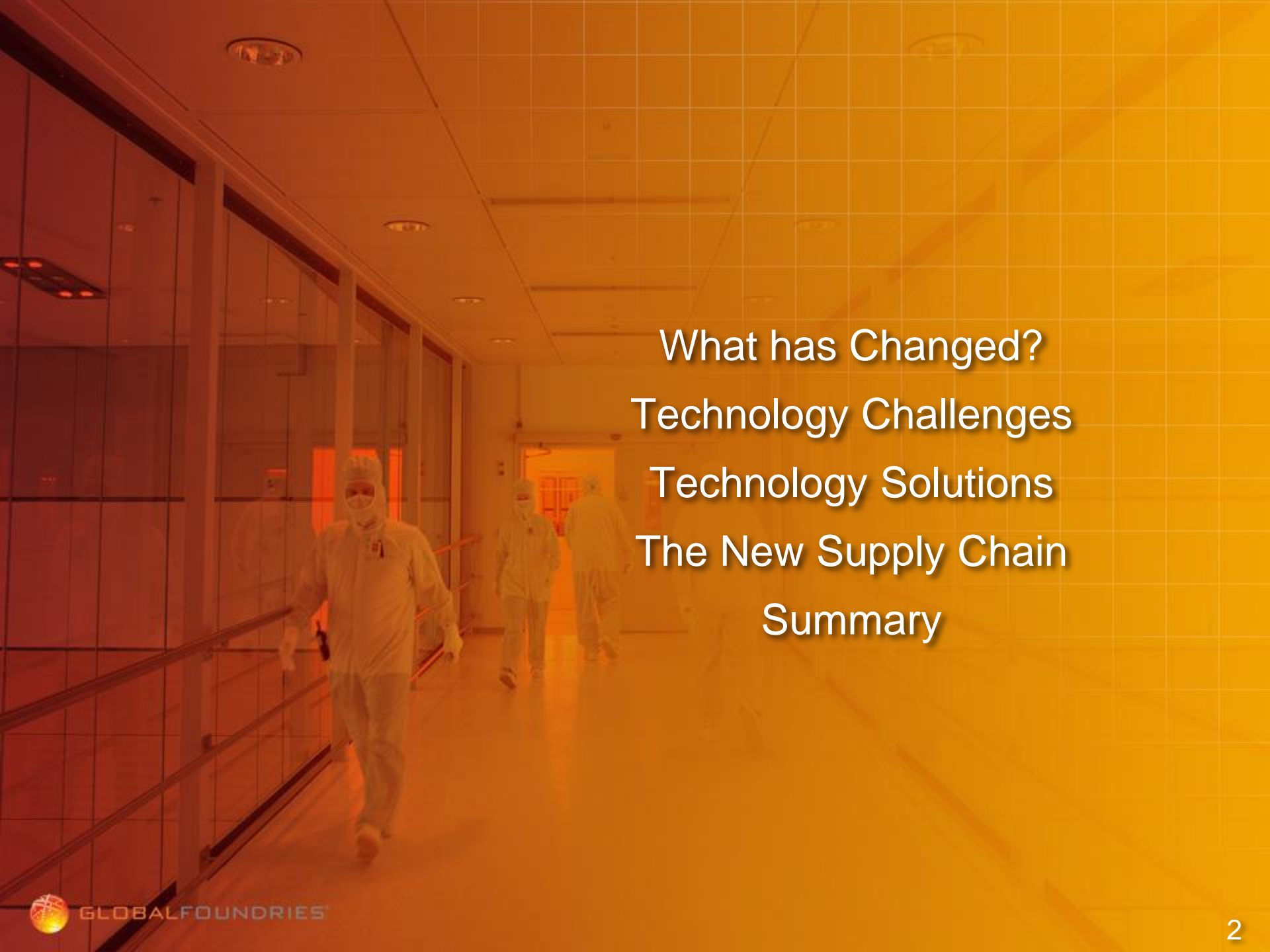


BRIDGING THE GAP BETWEEN SILICON AND PACKAGING

GREGG BARTLETT
CHIEF TECHNOLOGY OFFICER
GLOBALFOUNDRIES



GLOBALFOUNDRIES®

A photograph of a long, brightly lit hallway with a grid ceiling and recessed lights. Several people wearing full white protective suits, including hoods and masks, are walking away from the camera down the hallway. The scene is overlaid with a semi-transparent orange grid pattern.

What has Changed?
Technology Challenges
Technology Solutions
The New Supply Chain
Summary

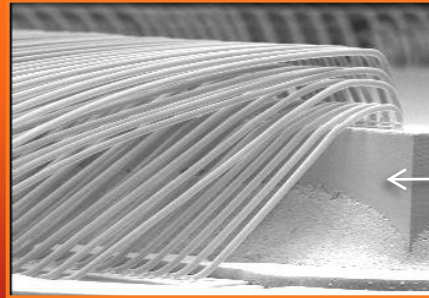


Silicon Interconnect Evolution

Interconnect process optimized by assembly provider with little or no Foundry involvement

Wire Bond: 2D

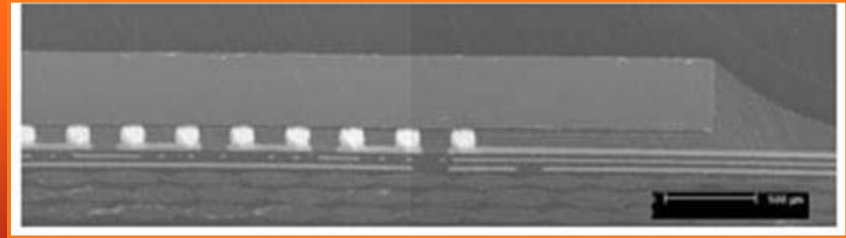
Typically 25-1000ea per IC



← Die Edge

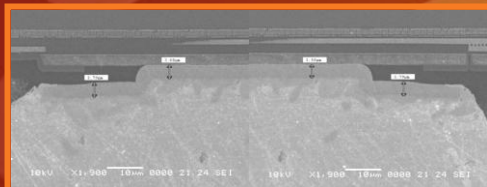
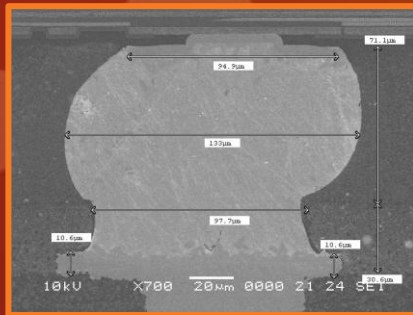
Flip Chip: 2D

Typically 250-10,000 per IC



Evolution to Flip Chip and Pb Free Bump: Driven by Performance and Interconnect Density

*Increasing collaboration between Foundry
and assembly provider for optimum solutions*



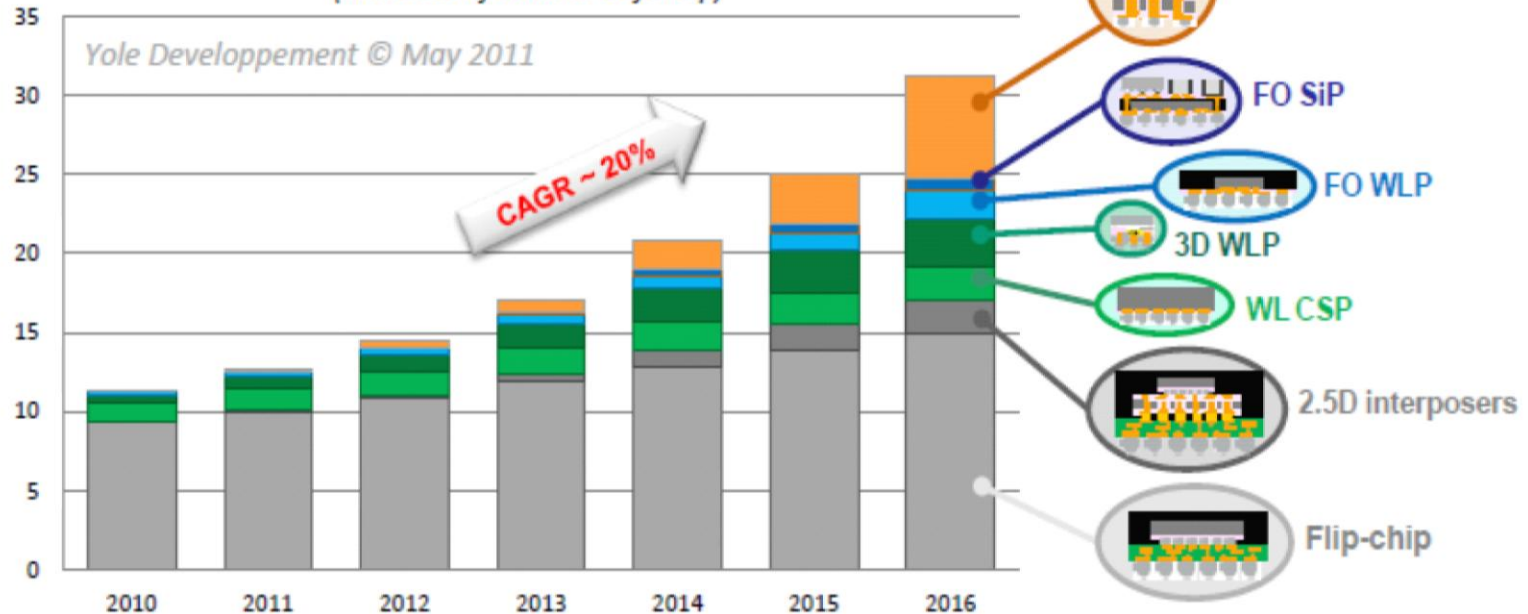
Impacts:

- Increased I/O density
- Improved electrical performance
- Higher modulus interconnect
- Weaker low K dielectric
- Substrate thickness and CTE have increasing role

Explosion of Wafer Level Products: Driven by I/O Density, Performance, Form Factor

Overall Wafer-Level-Packaging demand

(in Munits of 300mm wafer eq.)

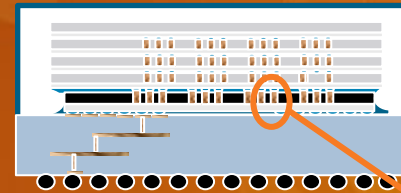


Driving Revolution to Silicon Interconnect

Interconnect solutions require high collaboration between Foundry-OSAT

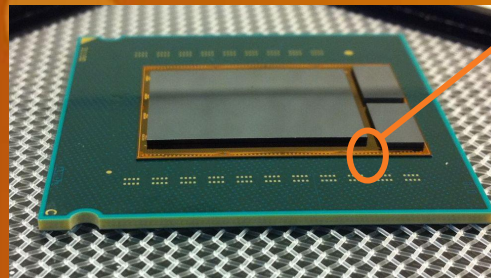
Through Silicon Via (TSV): 3D

Typically 1000-50,000 per IC



Through Silicon Via (TSV): 2.5D

TSV's in interposer



TSV's

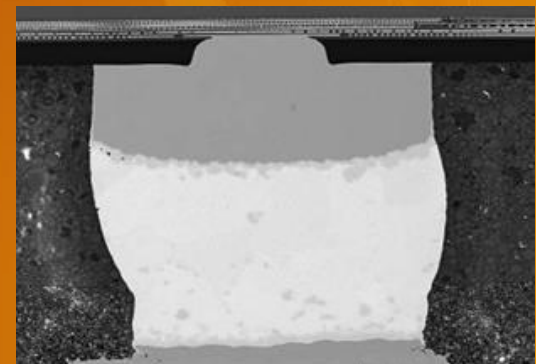
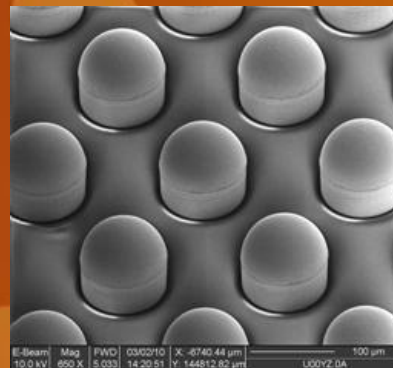
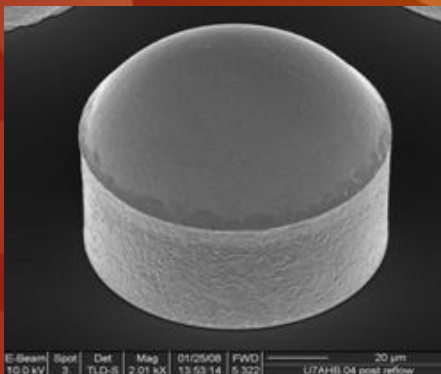
Requiring New Technologies

New interconnect at much finer pitch

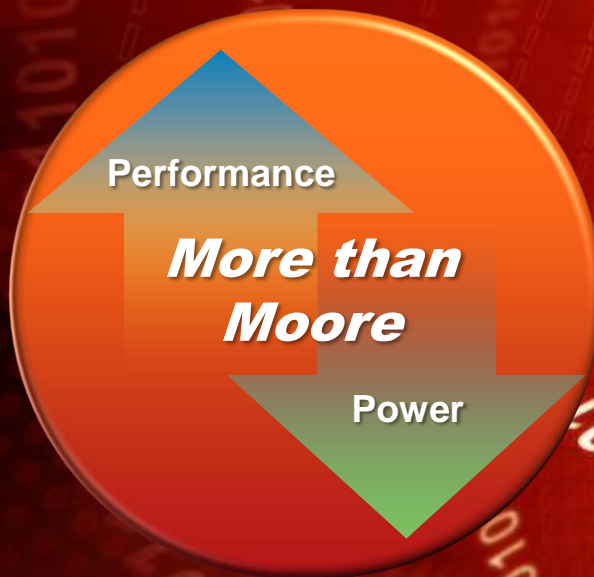
Probe (wafer test) as fine pitch

Thin wafer handling

New assembly technologies and design rules to manage warpage



Technology Challenges



System Level Performance and Bandwidth

Video and data packet processing are driving need for faster memory access

Graphics, Mobile Video, Networking Processors, FPGA

Power becoming costly for performance and mobile applications

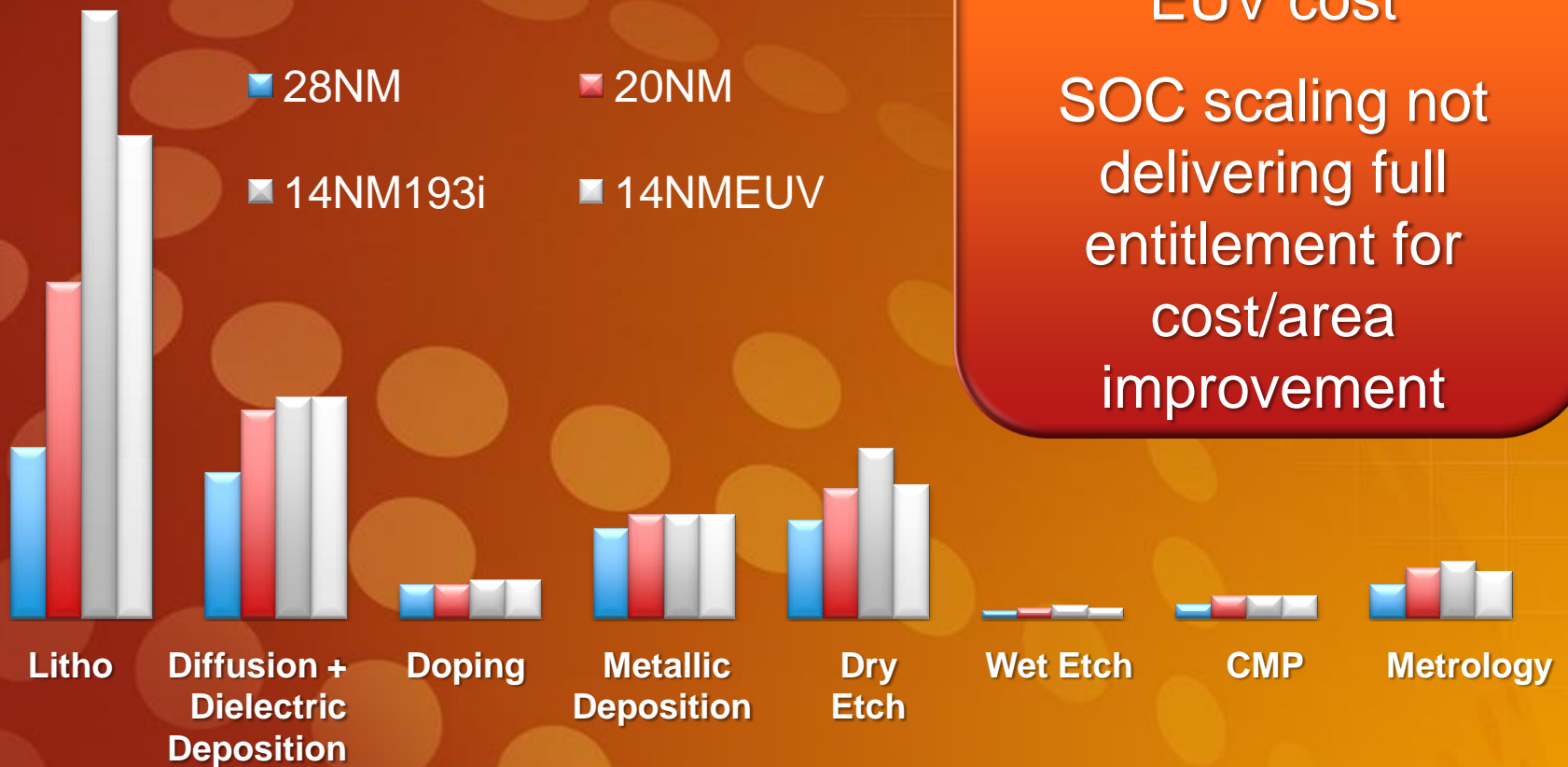
Digital scaling and performance (for video/data) outstripping memory capacity

Power consumed by logic and memory reducing battery life

Increasing power required for logic and memory



Increasing Cost, Reducing Benefit of Scaling



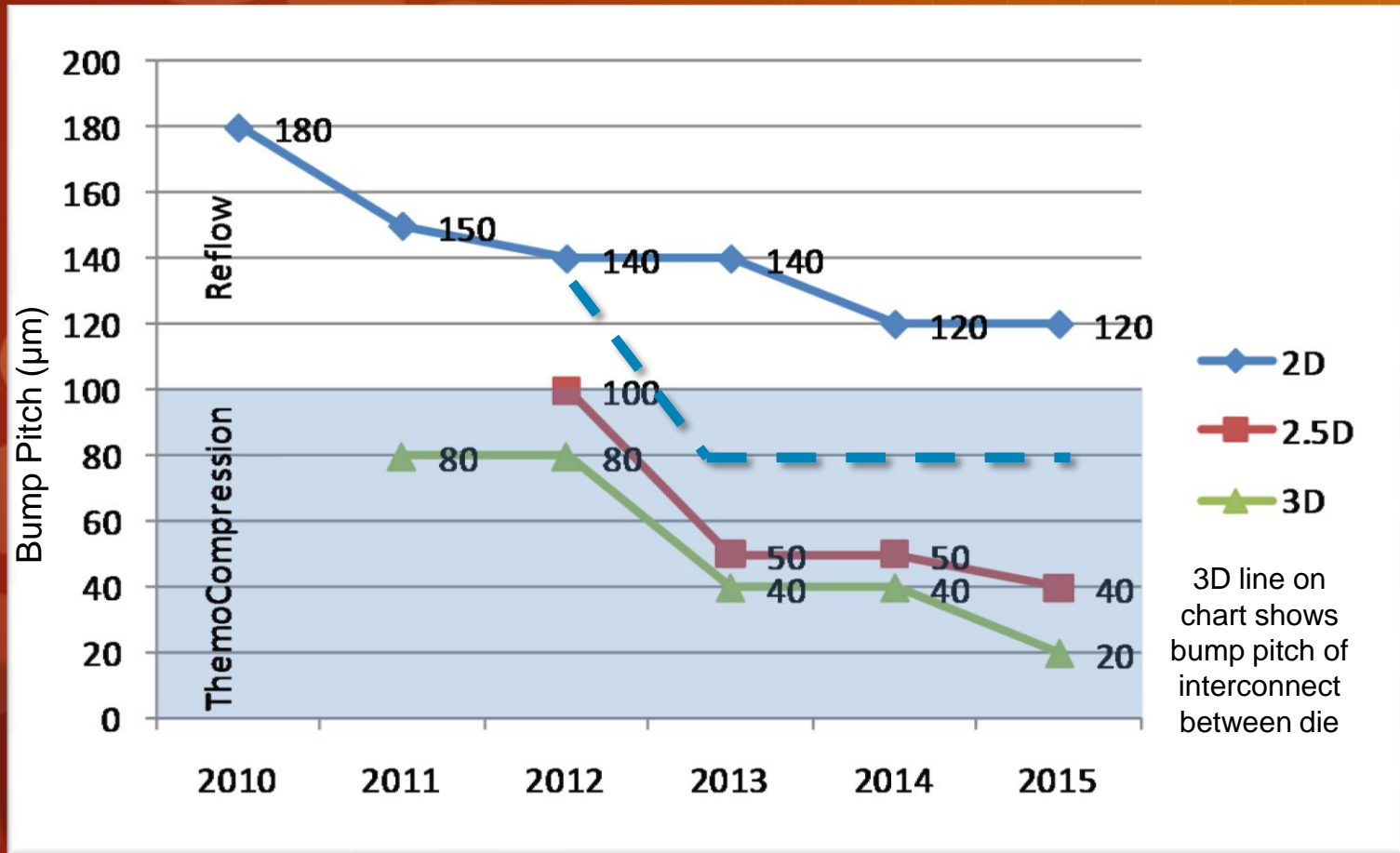
Double patterning,
EUV cost

SOC scaling not
delivering full
entitlement for
cost/area
improvement

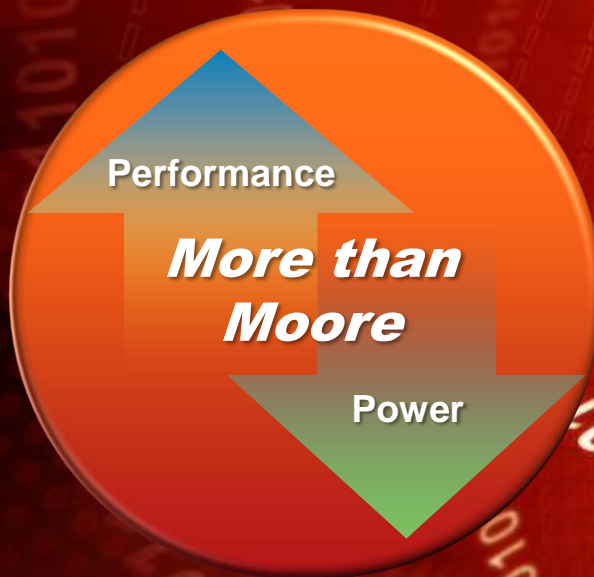
I/O Density Trend Drives Packaging

Shrinking pitch drives non-collapsing and smaller bumps

Smaller bumps increase warpage management risk



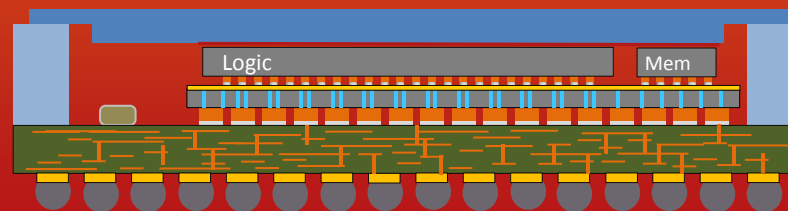
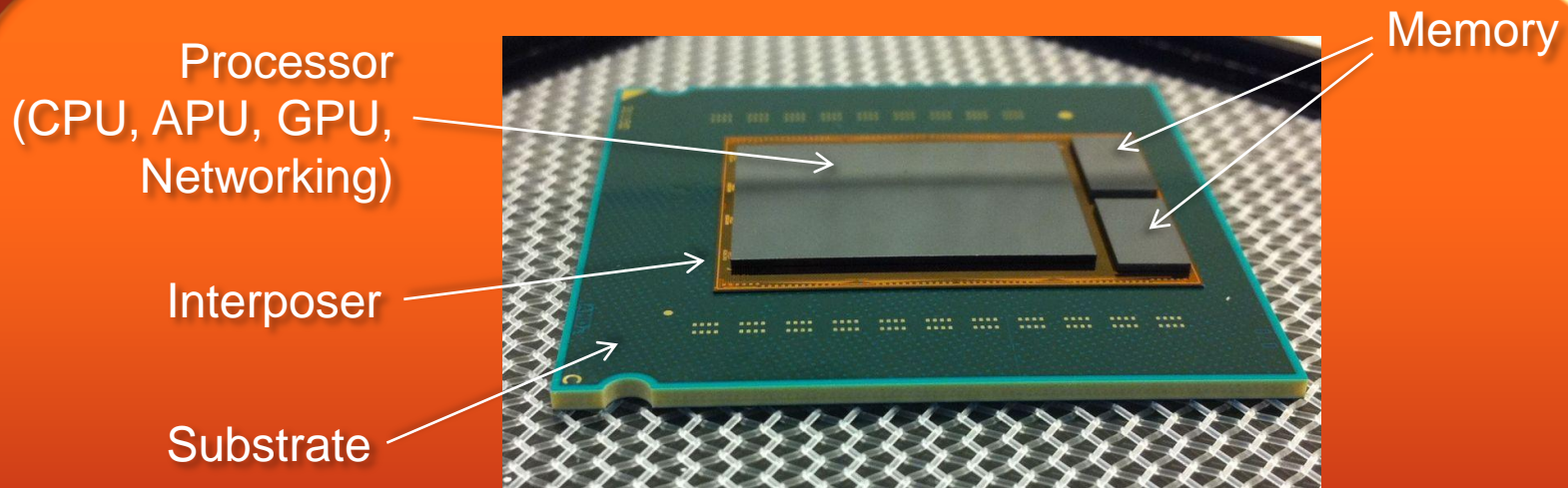
Solutions: Innovation, Cost, Collaboration



Memory Bandwidth Solution for High Power Applications: 2.5D

Interposer is “passive silicon” with TSV’s used for high density interconnect.

Main challenges are warpage of thin interposer and yield.



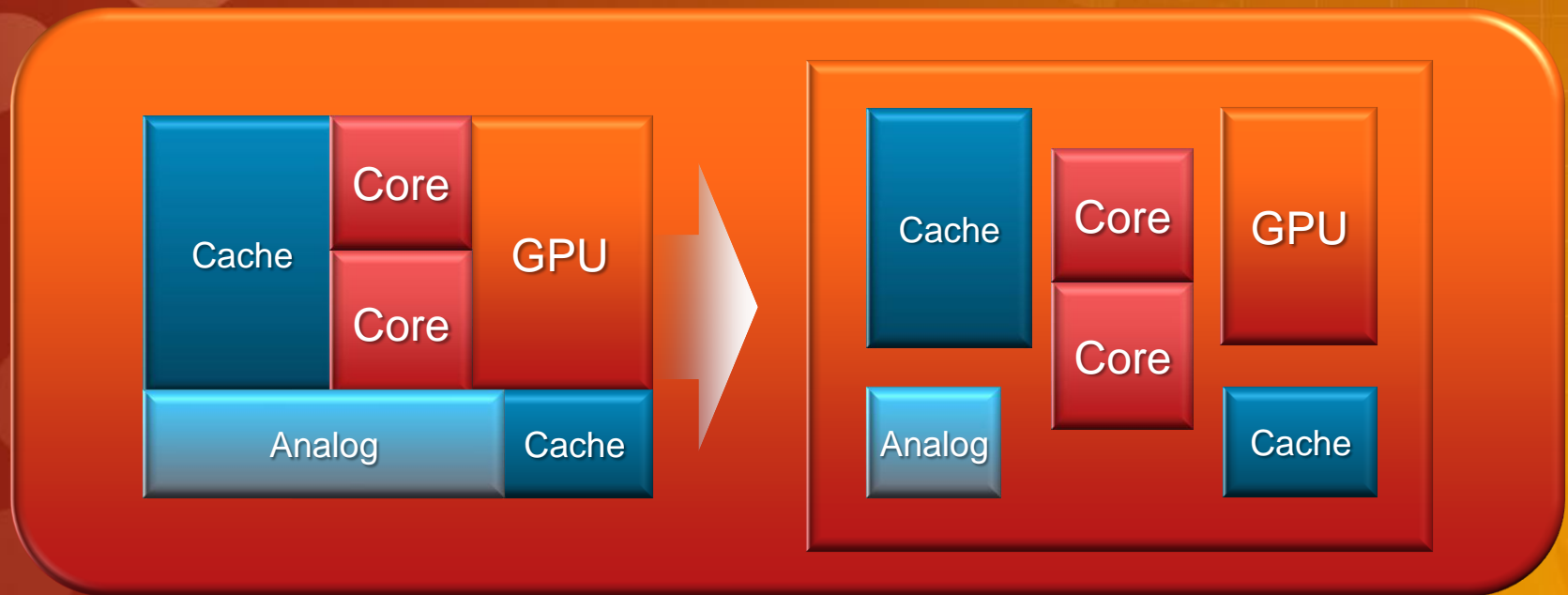
2.5D Enables “Fission”

Smaller die, higher yield, lower cost

Utilize process which is optimal for each function

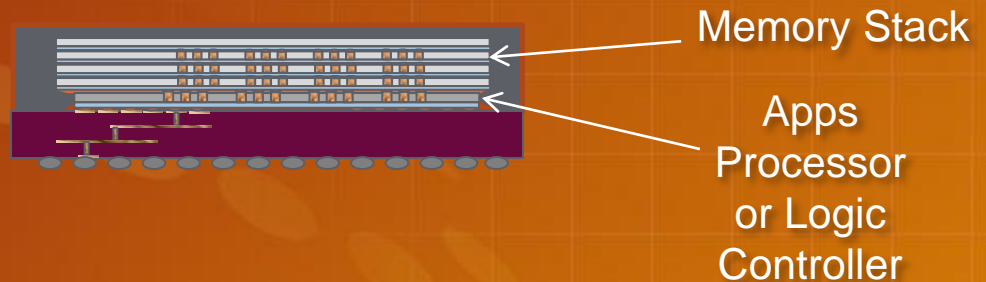
Scale each function when required, not whole SOC

Derive savings at system level as well: board, substrates, power



Memory Bandwidth Solution for Low Power Applications: 3D

3D: Vertical stacking of (mostly) logic and memory die. TSV's in logic die.



TSV's (Through-Silicon-Vias): Vertical connections through silicon, for very high interconnect density between IC's.

Wide I/O standard is 6um diameter with pitch 40-100um

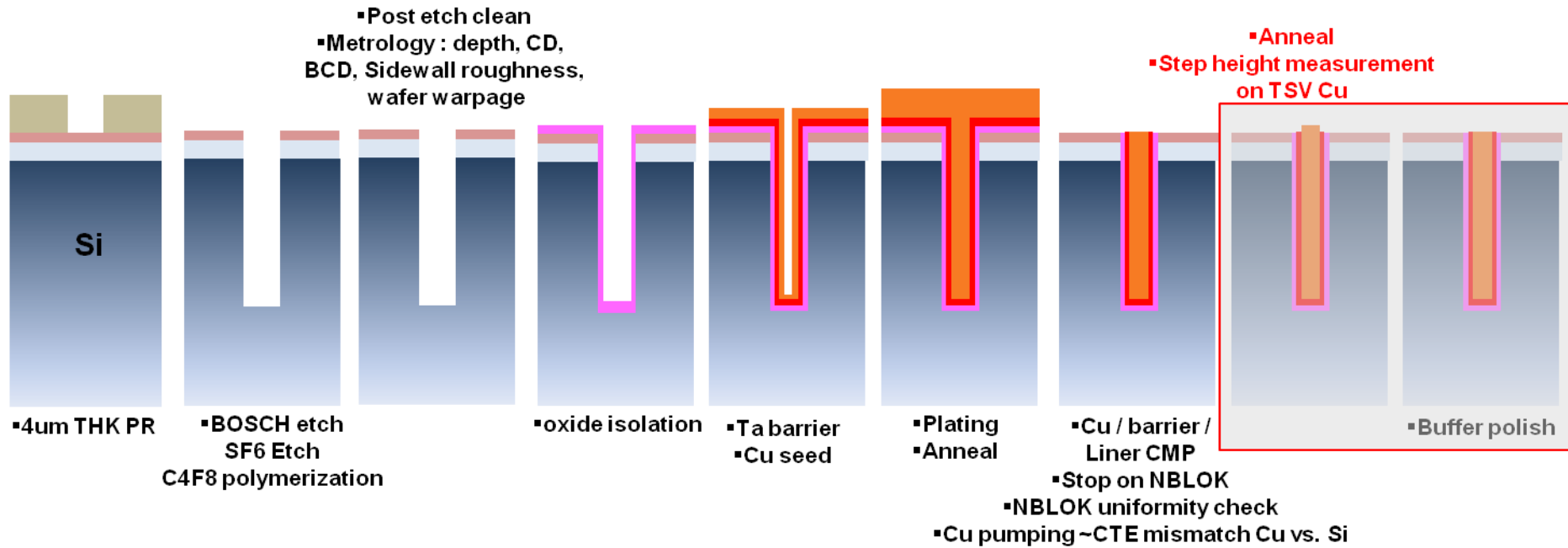
Much higher interconnect density increases bandwidth

Much shorter interconnect improves performance

Increased bandwidth reduces power



TSV Formation



Step height measurement for
 Cu pumping detection,
 Buffer polish and 2nd anneal
 can be skipped

TSV Process Development

Module development at consortia

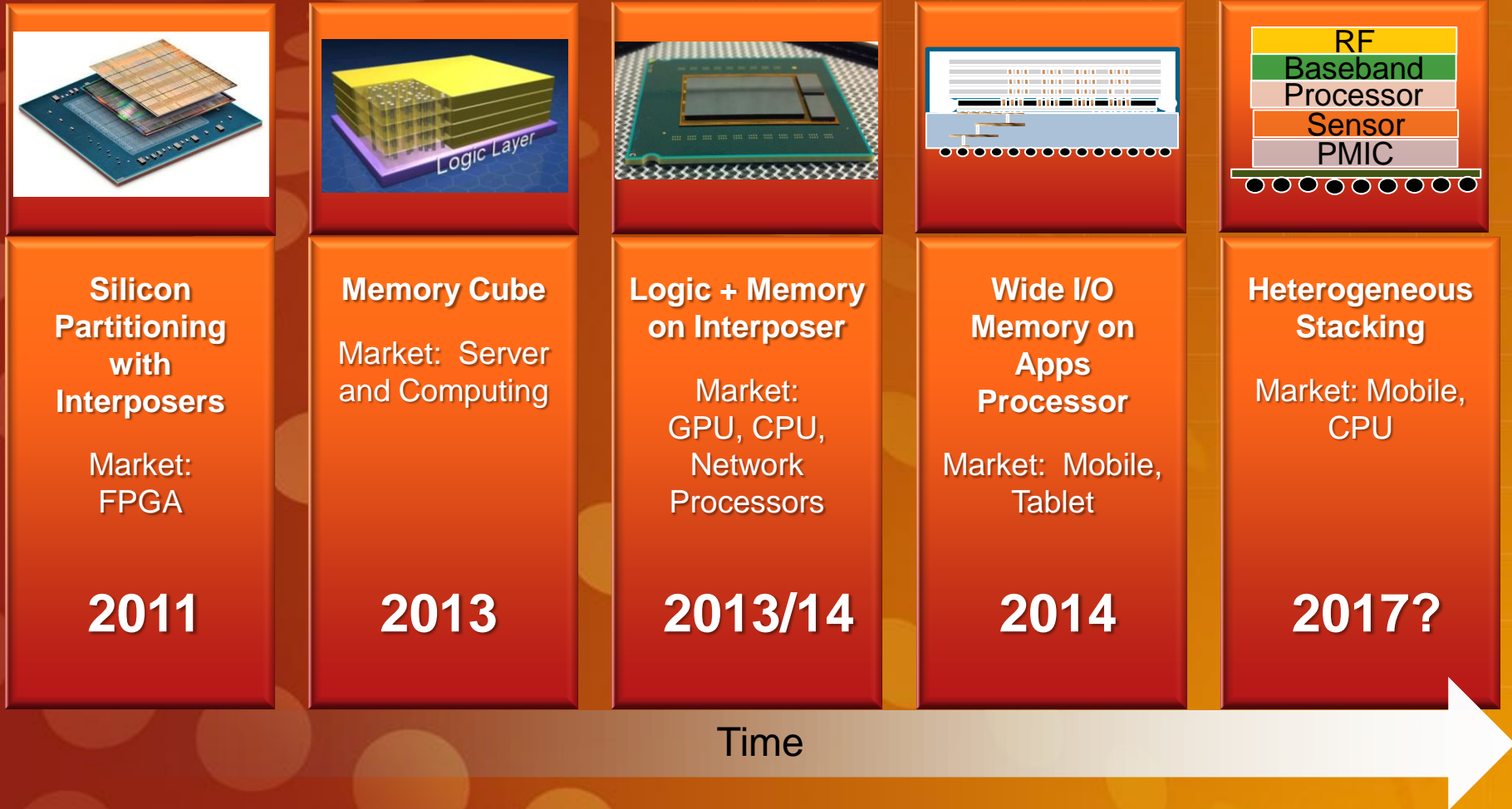
Integration in Foundry



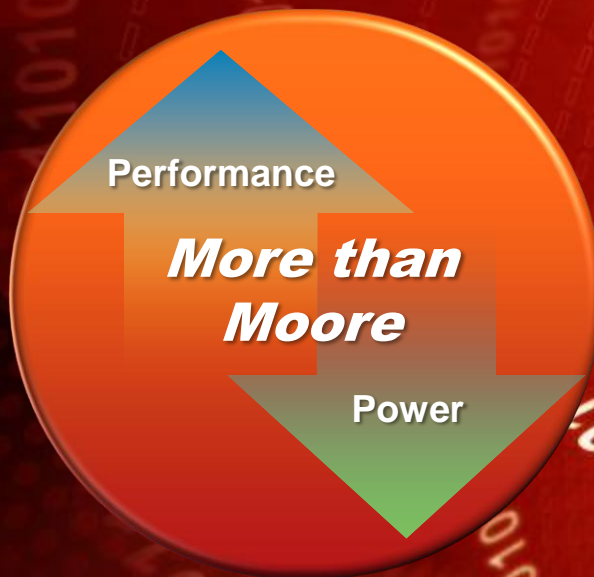
Collaboration between consortia, foundry, tool manufacturer critical

TSV Etch installed, Fab 8, NY

Packaging Roadmap

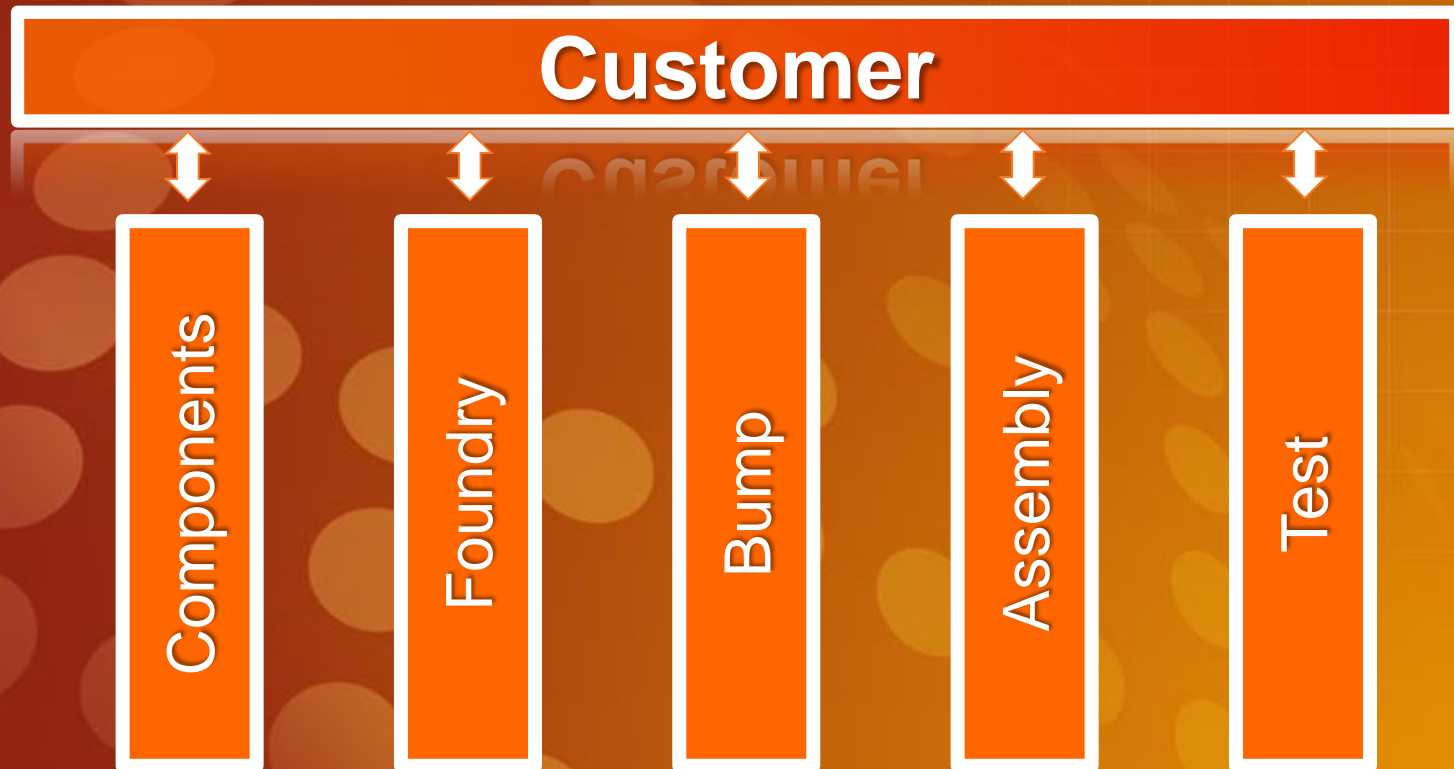


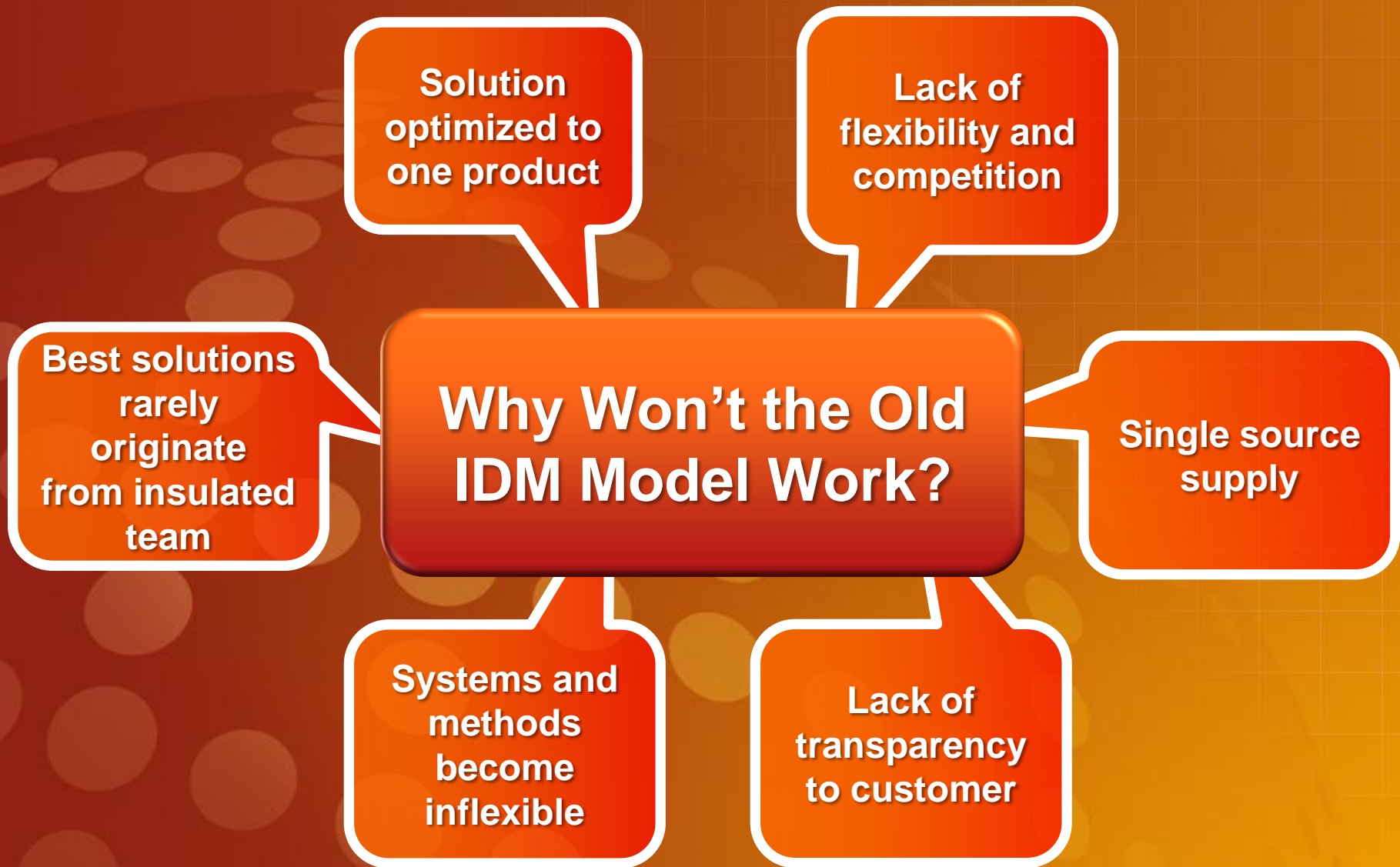
The New Supply Chain



Why Won't the Current Model Work?

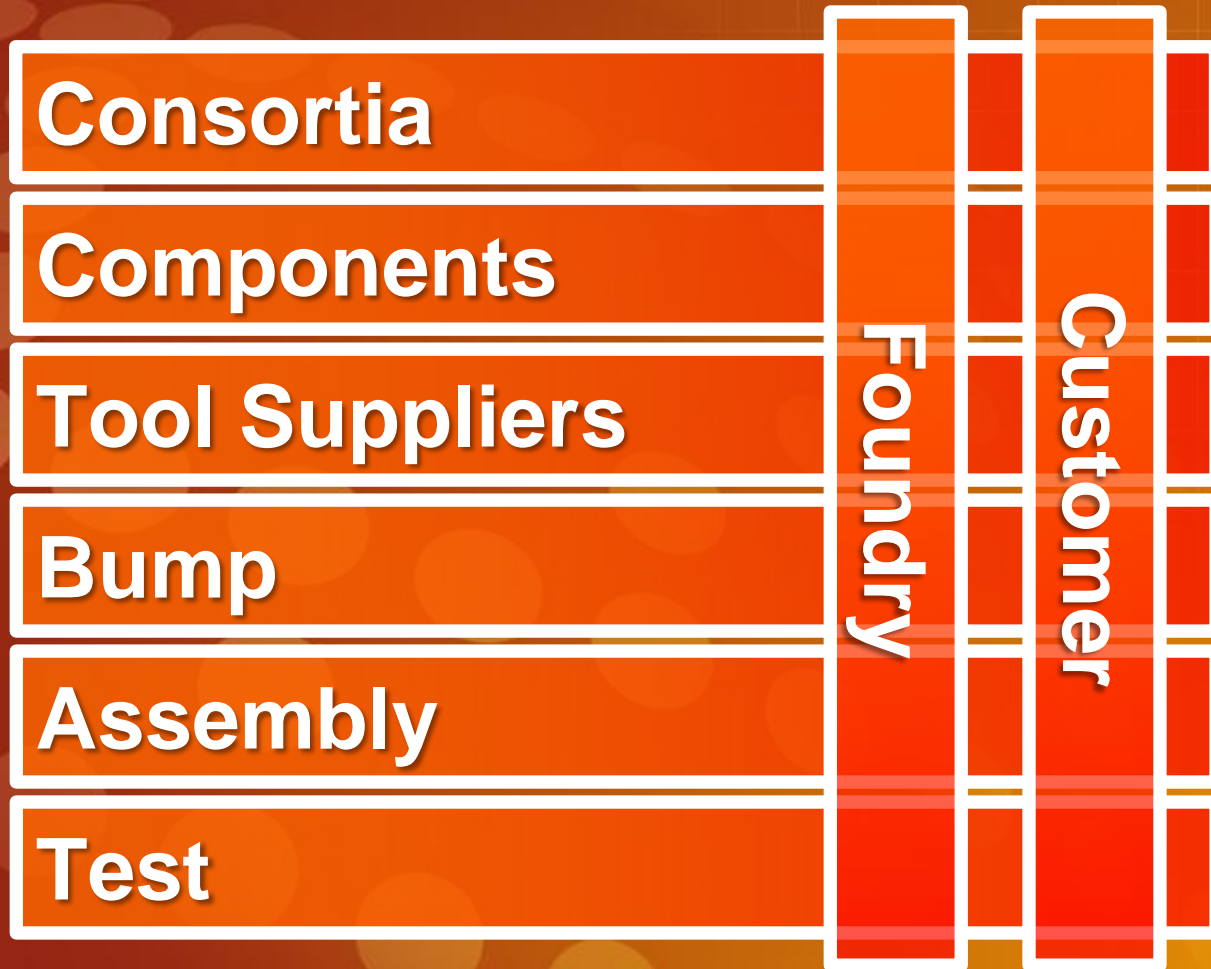
Solutions developed in isolation are no longer adequate to address the complexity of high-silicon content packaging



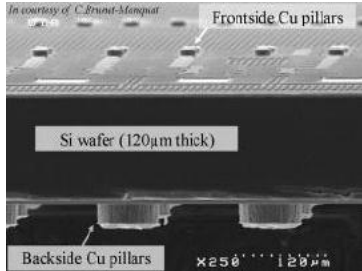


The New Model

Will Likely See Supply Chain Alliances Within the Industry



Collaborative Solutions Utilizing the Best Minds

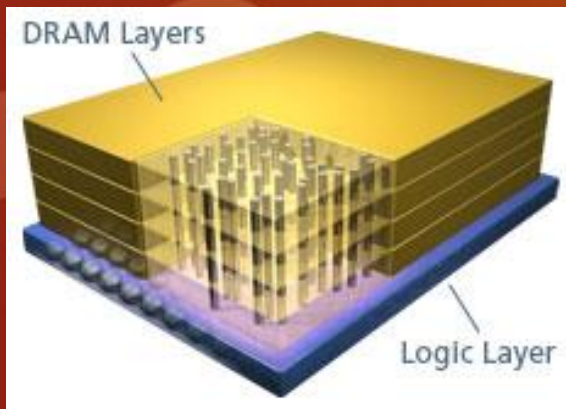


	Optimize Block Placement	Optimize TSV/Bump Placement	PDKs	Reference Flow	TSV Development	TSV Metrology	TSV Impact on Transistors	Thinning Impact on Transistors	KGD Methods	Fine Pitch Probe	Thin Wafer Handling	Assembly Development	Test Strategy and IP	Test Repairability
Consortia	Orange	Orange			Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange
Customers	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange					Orange
EDA Tool Suppliers	Orange	Orange	Orange	Orange	Orange									
MOL Tool Suppliers					Orange	Orange	Orange			Orange				
Assm Tool Suppliers											Orange	Orange	Orange	Orange
Foundry	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange
OSATs			Orange											
Memory Suppliers	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange	Orange
Test Tool Suppliers									Orange	Orange		Orange	Orange	Orange

Collaboration: Design for Yield



Co-Locate to Develop Solutions for Customers



Bring foundry and partners together to develop new tools, processes, and technologies for joining silicon

Fast learning cycles

Develop BEOL, bump, BSI, 3D assembly, test, and metrology together in one location for best collaborative ideas and evaluation of potential solutions

Development of thin wafer (50 μ m) handling tools and methods

Value Creation: Deliver Solutions to Customers





Thank You

Trademark Attribution

GLOBALFOUNDRIES, the GLOBALFOUNDRIES logo and combinations thereof are trademarks of GLOBALFOUNDRIES Inc. in the United States and/or other jurisdictions. Other names used in this presentation are for identification purposes only and may be trademarks of their respective owners.

©2012 GLOBALFOUNDRIES Inc. All rights reserved.